Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection
- AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V _{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	220	mA	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	2.2	3	Ω	

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		D1 D2
2	G1	gate 1	654	
3	D2	drain 2		G1 A A PL G2
4	S2	source 2	0	\
5	G2	gate 2	1 2 3	
6	D1	drain 1	TSSOP6 (SOT363)	S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BSS138AKS-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BSS138AKS-Q	J4%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or					
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	220	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	160	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.8	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	270	mW
			[1]	-	310	mW
		T _{sp} = 25 °C		-	1.3	W
Per device	-					
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	405	mW
T _j	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source Drai	n Diode (per transistor)					
I _S	source current	T _{amb} = 25 °C	[1]	-	210	mA
ESD maximi	um rating (per transistor)					
V _{ESD}	electrostatic discharge voltage	НВМ		-	500	V
Avalanche r	uggedness (per transistor)					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 20 mA; DUT in avalanche (unclamped)		-	6.6	mJ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

60 V, dual N-channel Trench MOSFET

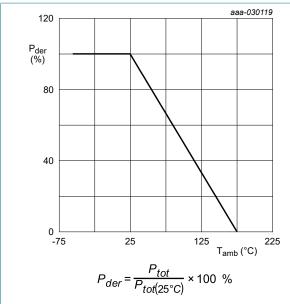


Fig. 1. Normalized total power dissipation as a function of ambient temperature

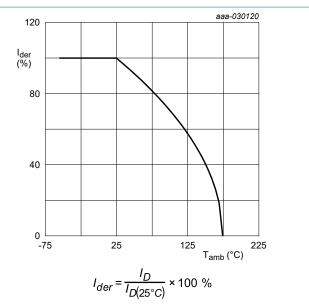


Fig. 2. Normalized continuous drain current as a function of ambient temperature

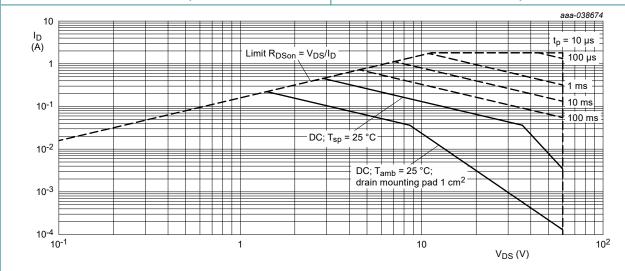


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device					'	'	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	375	K/W
Per transisto	or			,			
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	500	560	K/W
	junction to ambient		[2]	-	450	480	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	80	115	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

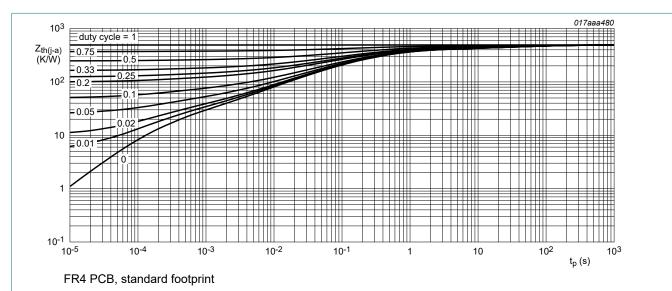


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

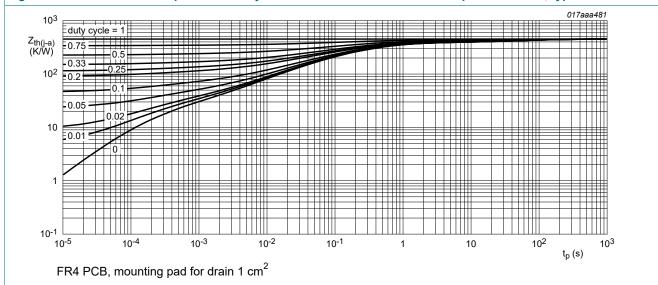


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.1	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	500	nA
	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C	-	-	5	μΑ	
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	500	nA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-500	nA
Doon	drain-source on-state	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	2.2	3	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 175 °C	-	4.6	6.3	Ω
		V _{GS} = 4.5 V; I _D = 50 mA; T _j = 25 °C	-	2.7	3.9	Ω
		V _{GS} = 2.5 V; I _D = 10 mA; T _j = 25 °C	-	3.4	12	Ω
g _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	0.3	-	S
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 100 mA; V _{GS} = 10 V;	-	0.21	0.315	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.022	-	nC
Q _{GD}	gate-drain charge		-	0.051	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	9	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	1.8	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
d(on)	turn-on delay time	V _{DS} = 30 V; I _D = 100 mA; V _{GS} = 10 V;	-	1	-	ns
r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	1	-	ns
d(off)	turn-off delay time	1	-	2	-	ns
t _f	fall time	1	-	3	-	ns
Source-dra	in diode			1	1	
V _{SD}	source-drain voltage	I _S = 210 mA; V _{GS} = 0 V; T _i = 25 °C	-	1	1.7	V
t _{rr}	reverse recovery time	$I_S = 210 \text{ mA}; dI_S/dt = -100 \text{ A/µs};$	-	7	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}$	_	1	_	nC

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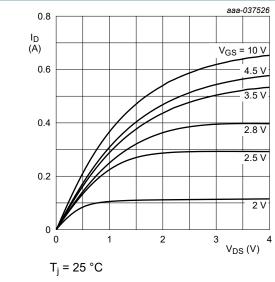


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

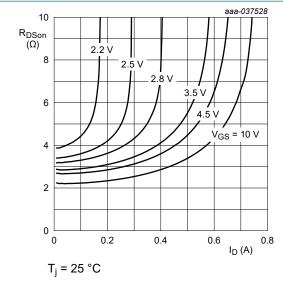


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

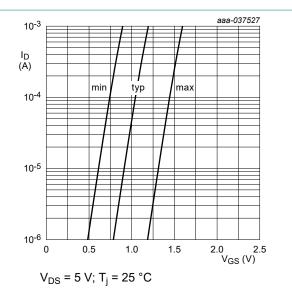


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

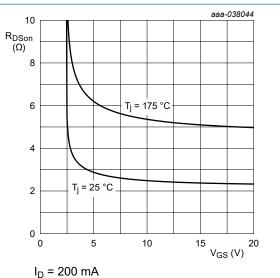


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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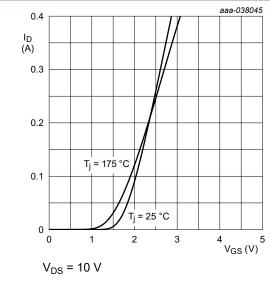


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

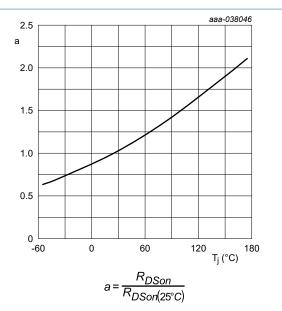


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

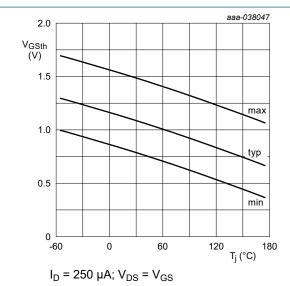


Fig. 12. Gate-source threshold voltage as a function of junction temperature

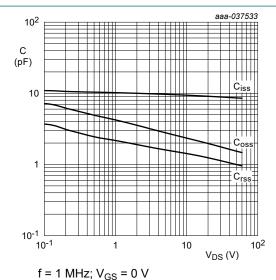


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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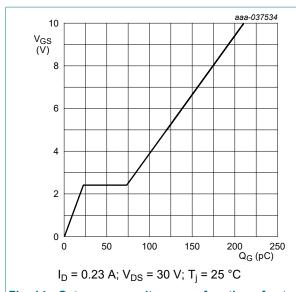


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

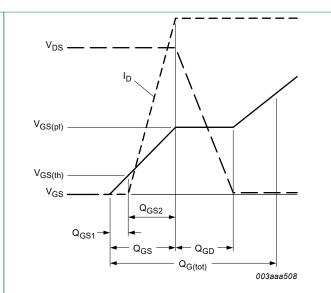


Fig. 15. Gate charge waveform definitions

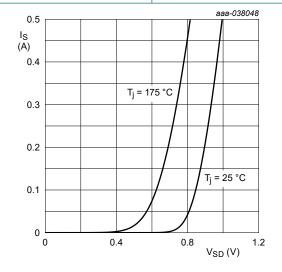
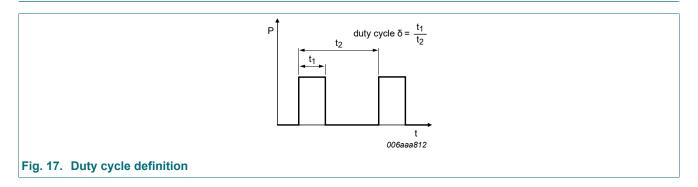


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

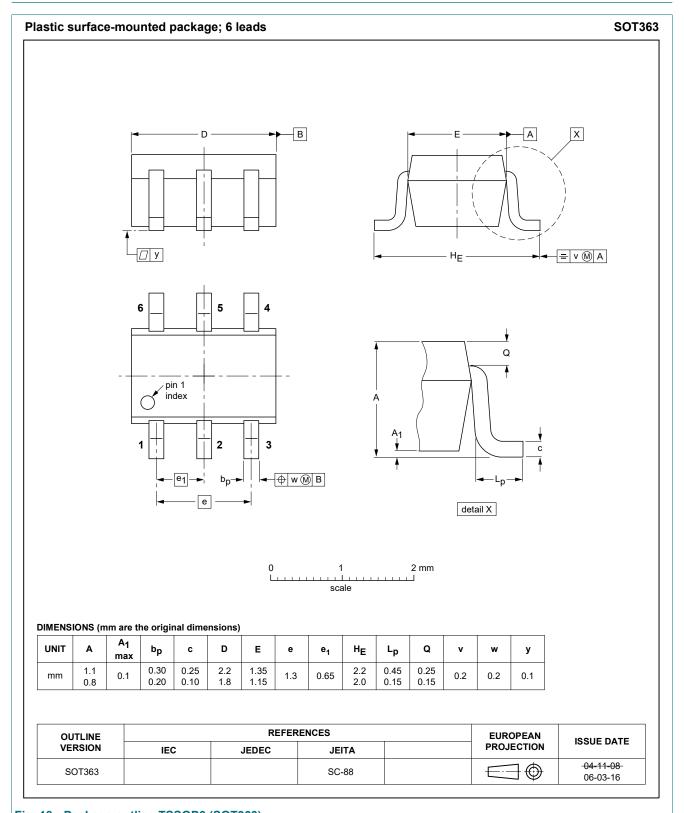
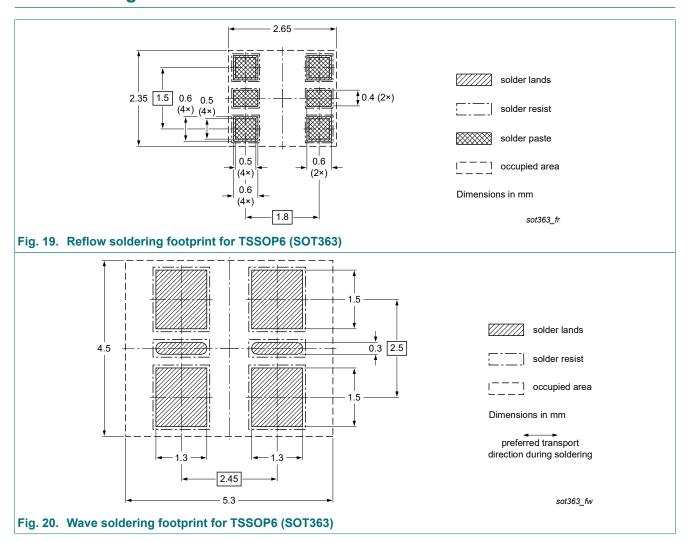


Fig. 18. Package outline TSSOP6 (SOT363)

60 V, dual N-channel Trench MOSFET

13. Soldering



60 V, dual N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSS138AKS-Q v.1	20240216	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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